

Fast turn-off Thyristor

P0366WC04# to P0366WC08#

The data sheet on the subsequent pages of this document is a scanned copy of existing data for this product.

(Rating Report 83TR3 Issue 4)

This data reflects the old part number for this product which is: P214CH02-08. This part number must **NOT** be used for ordering purposes – please use the ordering particulars detailed below.

The limitations of this data are as follows:

Device no longer available for grade 02 (200V V_{RRM}/V_{DRM})

Please use the following link to view an up to date outline drawing for this device

[Outline W8](#)

Where any information on the product matrix page differs from that in the following data, the product matrix must be considered correct

An electronic data sheet for this product is presently in preparation.

For further information on this product, please contact your local ASM or distributor.

Alternatively, please contact Westcode as detailed below.

Ordering Particulars			
P0366	WC	◆◆	#
Fixed Type Code	Fixed Outline Code	Voltage code $V_{DRM}/100$ 04-08	Fixed Turn-off Time Code A = 10 μ s, B = 12 μ s, C = 15 μ s
Typical Order Code: P0366WC06B, 14mm clamp height, 600V V_{RRM}/V_{DRM} , 12 μ s t_q			

IXYS Semiconductor GmbH
Edisonstraße 15
D-68623 Lampertheim
Tel: +49 6206 503-0
Fax: +49 6206 503-627
E-mail: marcom@ixys.de

WESTCODE
An  IXYS Company

Westcode Semiconductors Ltd
Langley Park Way, Langley Park,
Chippenham, Wiltshire, SN15 1GE.
Tel: +44 (0)1249 444524
Fax: +44 (0)1249 659448
E-mail: WSL.sales@westcode.com

IXYS Corporation
3540 Bassett Street
Santa Clara CA 95054 USA
Tel: +1 (408) 982 0700
Fax: +1 (408) 496 0670
E-mail: sales@ixys.net

www.westcode.com

www.ixys.com

Westcode Semiconductors Inc
3270 Cherry Avenue
Long Beach CA 90807 USA
Tel: +1 (562) 595 6971
Fax: +1 (562) 595 8182
E-mail: WSI.sales@westcode.com

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In the interest of product improvement, Westcode reserves the right to change specifications at any time without prior notice.

Devices with a suffix code (2-letter, 3-letter or letter/digit/letter combination) added to their generic code are not necessarily subject to the conditions and limits contained in this report.



WESTCODE SEMICONDUCTORS

Technical
Publication
TP214C

Inverter Grade Capsule Thyristor Type P214C

370 amperes average: up to 800 volts V_{RRM}/V_{DRM}

Ratings (Maximum values at 125°C T_j unless stated otherwise)

RATING	CONDITIONS	SYMBOL	
Average on-state current	Half sine wave $\left\{ \begin{array}{l} 55^{\circ}\text{C heatsink temperature} \\ \text{(double side cooled)} \\ 85^{\circ}\text{C heatsink temperature} \\ \text{(single side cooled)} \end{array} \right.$	$I_{T(AV)}$	370 A 130 A
R.M.S. on-state current	25°C heatsink temperature, double side cooled	$I_{T(RMS)}$	756 A
Continuous on-state current	25°C heatsink temperature, double side cooled	I_T	590 A
Peak one-cycle surge (non-repetitive) on state current	10ms duration, 60% V_{RRM} re-applied 10ms duration, $V_R \leq 10$ volts	$I_{TSM(1)}$ $I_{TSM(2)}$	4700 A 5170 A
Maximum permissible surge energy	10ms duration, $V_R \leq 10$ volts 3ms duration, $V_R \leq 10$ volts	$I^2t(1)$ $I^2t(2)$	134000 A ² s 98000 A ² s
Peak forward gate current	Anode positive with respect to cathode	I_{FGM}	18 A
Peak forward gate voltage	Anode positive with respect to cathode	V_{FGM}	12 V
Peak reverse gate voltage		V_{RGM}	5 V
Average gate power		P_G	1.5 W
Peak gate power	100μs. pulse width	P_{GM}	60 W
Rate of rise of off-state voltage	To 80% V_{DRM} gate open-circuit	dv/dt	*200 V/μs
Rate of rise of on-state current (repetitive)	$\left\{ \begin{array}{l} \text{Gate drive 20 volts, 20 ohms with } t_r \leq 1\mu\text{s.} \\ \text{Anode voltage } \leq 80\% V_{DRM} \end{array} \right.$	$di/dt(1)$	500 A/μs
Rate of rise of on-state current (non-repetitive)		$di/dt(2)$	1000 A/μs
Operating temperature range		T_{hs}	-40 + 125°C
Storage temperature range		T_{stg}	-40 + 150°C

Characteristics (Maximum values at 125°C T_j unless stated otherwise)

CHARACTERISTIC	CONDITIONS	SYMBOL	
Peak on-state voltage	At 715 A, I_{TM}	V_{TM}	1.88 V
Forward conduction threshold voltage		V_O	1.40 V
Forward conduction slope resistance		r	0.67 mΩ
Repetitive peak off-state current	At V_{DRM}	I_{DRM}	30 mA
Repetitive peak reverse current	At V_{RRM}	I_{RRM}	30 mA
Maximum gate current required to fire all devices	$\left\{ \begin{array}{l} \text{At } 25^{\circ}\text{C, } V_A = \text{ } \\ 6\text{ V, } I_A = 1\text{ A} \end{array} \right.$	I_{GT}	200 mA
Maximum gate voltage required to fire all devices		V_{GT}	3 V
Maximum holding current		I_H	600 mA
Maximum gate voltage which will not trigger any device		V_{GD}	0.25 V
Stored charge	$I_{TM} = 300\text{ A, } di/dt \text{ 20 A/}\mu\text{s}$ $V_{RM} = 50\text{ V, 50\% chord value}$	Q_{rr} typical	25 μC
Circuit commutated turn-off time available down to	$I_{TM} = 300\text{ A}$ $di/dt = 20\text{ A/}\mu\text{s, } V_{RM} = 50\text{ V}$ $\left\{ \begin{array}{l} 200\text{ V/}\mu\text{s to } 80\% V_{DRM} \\ 20\text{ V/}\mu\text{s to } 80\% V_{DRM} \end{array} \right.$	t_q t_q typical	15-30 μs 10-20 μs
Thermal resistance, junction to heat sink, for a device with a maximum forward volt drop characteristic	Double side cooled Single side cooled	$R_{th(j-hs)}$	0.095°C/W 0.190°C/W

VOLTAGE CODE	H02	H03	H04	H06	H08			
Repetitive peak voltages Non-repetitive peak off-state voltage	V_{RRM} V_{DRM}	200	300	400	600	800		
Non-repetitive peak reverse blocking voltage	V_{RSM}	300	400	500	700	900		

Ordering Information (Please quote device code as explained below)

P	2	1	4	C	• • •	•	•	0
Fixed type code	Voltage Code (see ratings)	dv/dt code to 80% V_{DRM} C = 20V/μs E = 100V/μs D = 50V/μs F = 200V/μs		Turn-off time H = 30 μs J = 25 μs K = 20 μs L = 15 μs N = 10 μs				

Typical code: P214CH06FJ0 = 600 V_{RRM} 600 V_{DRM} 200 V/μs dv/dt to 80% V_{DRM} 25 μs turn-off

*Other values of dv/dt up to 1000 V/μs, and turn-off time may be available.

1. INTRODUCTION

The P214C thyristor series are diffused regenerative gate devices employing a 24 mm slice in a cold weld housing.

2. NOTES ON THE RATINGS

(a) Rate of rise of on-state current

The maximum un-primed rate of rise of on-state current must not exceed 1000 A/ μ s at any time during turn-on on a non-repetitive basis. For repetitive performance the on-state rate of rise of current must not exceed 500 A/ μ s at any time during turn-on. Note that these values of current rate of rise apply to the circuit external to the device and its specified snubber network and device current rates of rise will be higher.

(b) Square wave ratings

These ratings are given for leading edge linear rates of rise of forward current of 100 and 500 A/ μ s.

(c) Duty Cycle Lines

The 100% duty cycle line appears on all these ratings. These frequency ratings are presented in the form that all duty cycles may be represented by straight parallel lines.

(d) Maximum operating Frequency

The maximum operating frequency, f_{max} , is set by the time required for the thyristor to turn off (t_q) and for the off-state voltage to reach full value (t_v), i.e.

$$f_{max} = \frac{1}{t_{pulse} + t_q + t_v}$$

(e) Energy per pulse characteristics

These curves enable rapid estimation of device dissipation to be obtained for conditions not covered by the frequency ratings.

Let E_p be the Energy per pulse for a given current and pulse width, in joules.

Then $W_{AV} = E_p \times f$.

3. REVERSE RECOVERY LOSS

On account of the number of circuit variables affecting reverse recovery voltage, no allowance for reverse recovery loss has been made in these ratings. The following procedure is recommended for use where it is necessary to include reverse recovery loss.

(a) Determination by Measurement

From waveforms of recovery current obtained from a high frequency shunt (see Note 1) and reverse voltage present during recovery, an instantaneous reverse recovery loss waveform must be constructed. Let the area under this waveform be A joules per pulse. A new heat sink temperature can then be evaluated from:

$$T_{SINK} (new) = T_{SINK} (original) - A \left(\frac{r_t \cdot 10^6}{t} + R_{th} \times f \right)$$

where $r_t = 1.64 \times 10^{-4} \sqrt{t}$

t = duration of reverse recovery loss per pulse in microseconds

A = Area under reverse loss waveform per pulse in joules (W.S.)

f = rated frequency at the original heat sink temperature

The total dissipation is now given by

$$W_{(TOT)} = W_{(original)} + A \times f$$

(b) Design Method

In circumstances where it is not possible to measure voltage and current conditions, or for design purposes, the additional losses may be estimated from **page 10**. A typical R-C snubber network is connected across the thyristor to control the transient reverse voltage waveform.

Let E be the value of energy per reverse cycle in joules **page 10**.

Let f be the operating frequency in Hz

$$\text{then } T_{SINK} \text{ new} = T_{SINK} \text{ original} - ER_{th} \times f$$

where $T_{SINK} \text{ new}$ is the required maximum heat sink temperature

and $T_{SINK} \text{ original}$ is the heat sink temperature given with the frequency ratings.

4. GATE DRIVE

The recommended gate drive is 20 V, 20 ohms with a short-circuit current rise time of not more than 1 μ s. This gate drive must be applied when using the full di/dt capability of the device.

5. THE DV/DT SUPPRESSION NETWORK

The effect of a conventional resistor-capacitor snubber of 0.22 μ F 5 ohms has been included in these ratings and all rating di/dt values apply to the circuit external to the thyristor and its suppression network.

Snubber Network Values

A series connected C-R filter may be required across the anode to cathode terminals of the thyristor for the purpose of reducing off-state voltage overshoot.

The optimum values for C and R depend partly on the circuits connected to the thyristor. For most applications the snubber design values should not exceed a maximum of 0.22 μ F or a minimum of 5 ohms. Please consult Westcode for values outside these limits.

6. NOTE 1

REVERSE RECOVERY LOSS BY MEASUREMENT

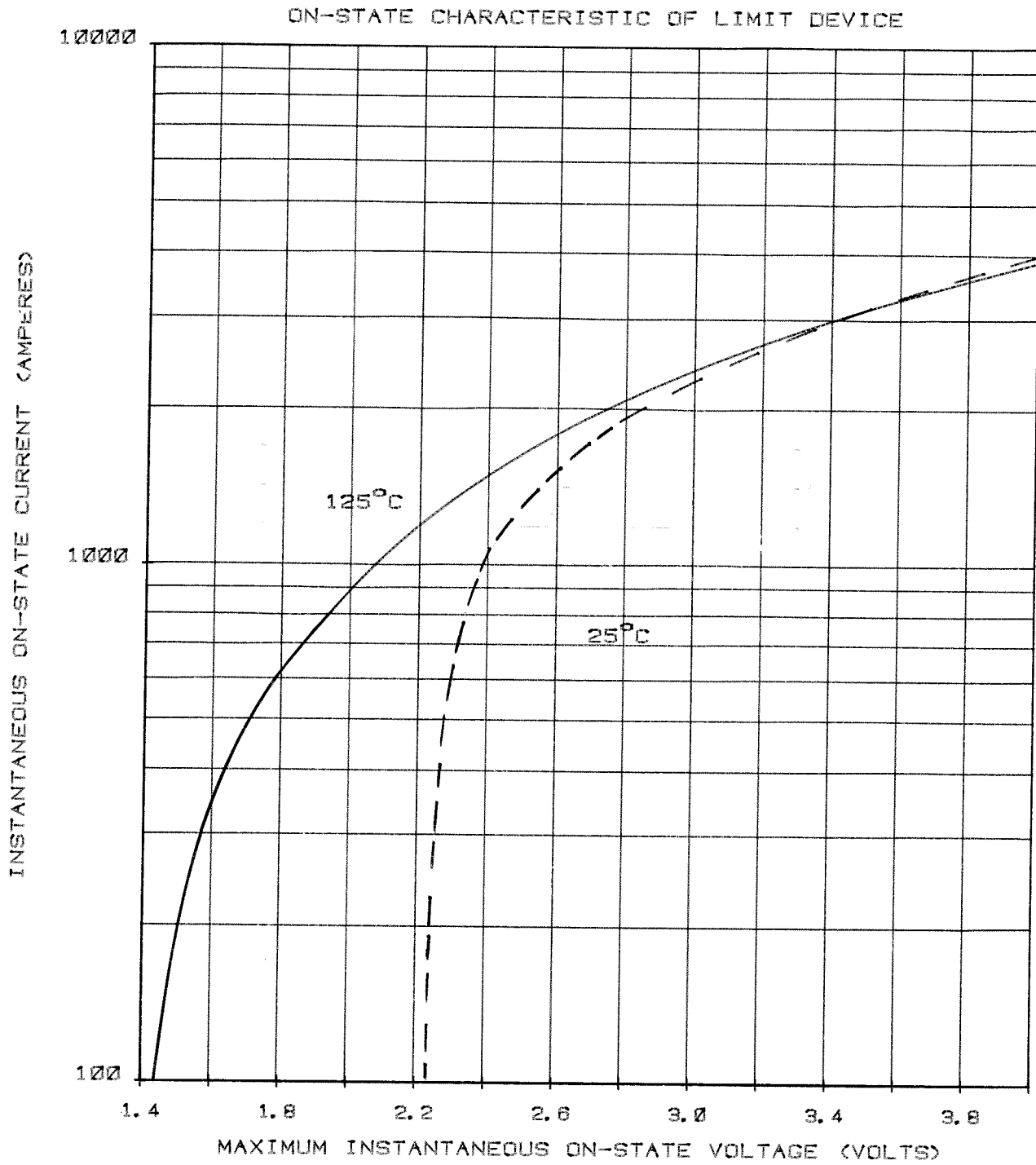
This thyristor has a low reverse recovered charge and peak reverse recovery current. When measuring the charge care must be taken to ensure that:

(a) a.c. coupled devices such as current transformers are not affected by prior passage of high amplitude forward current.

(b) The measuring oscilloscope has adequate dynamic range — typically 100 screen heights — to cope with the initial forward current without overload.

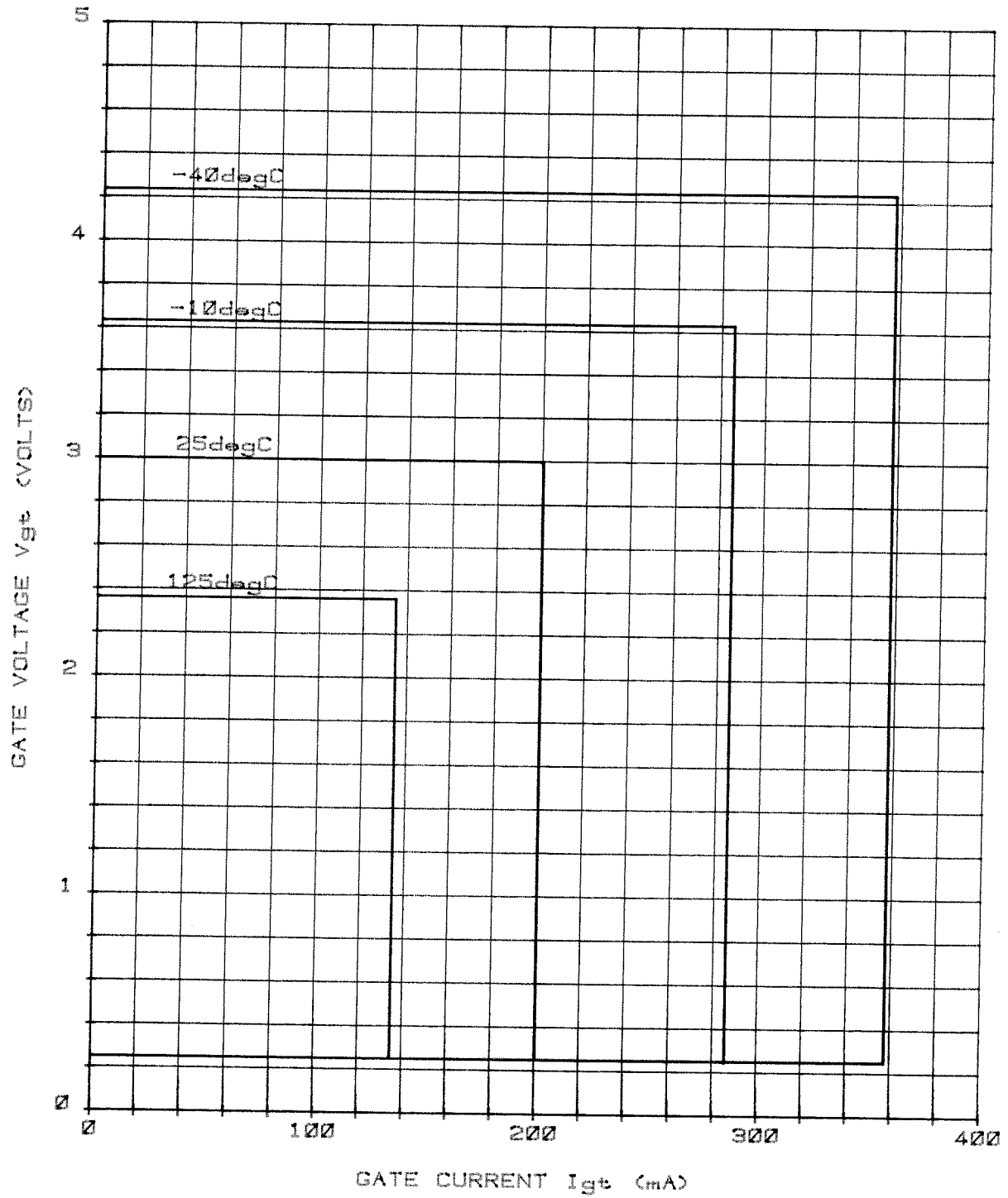
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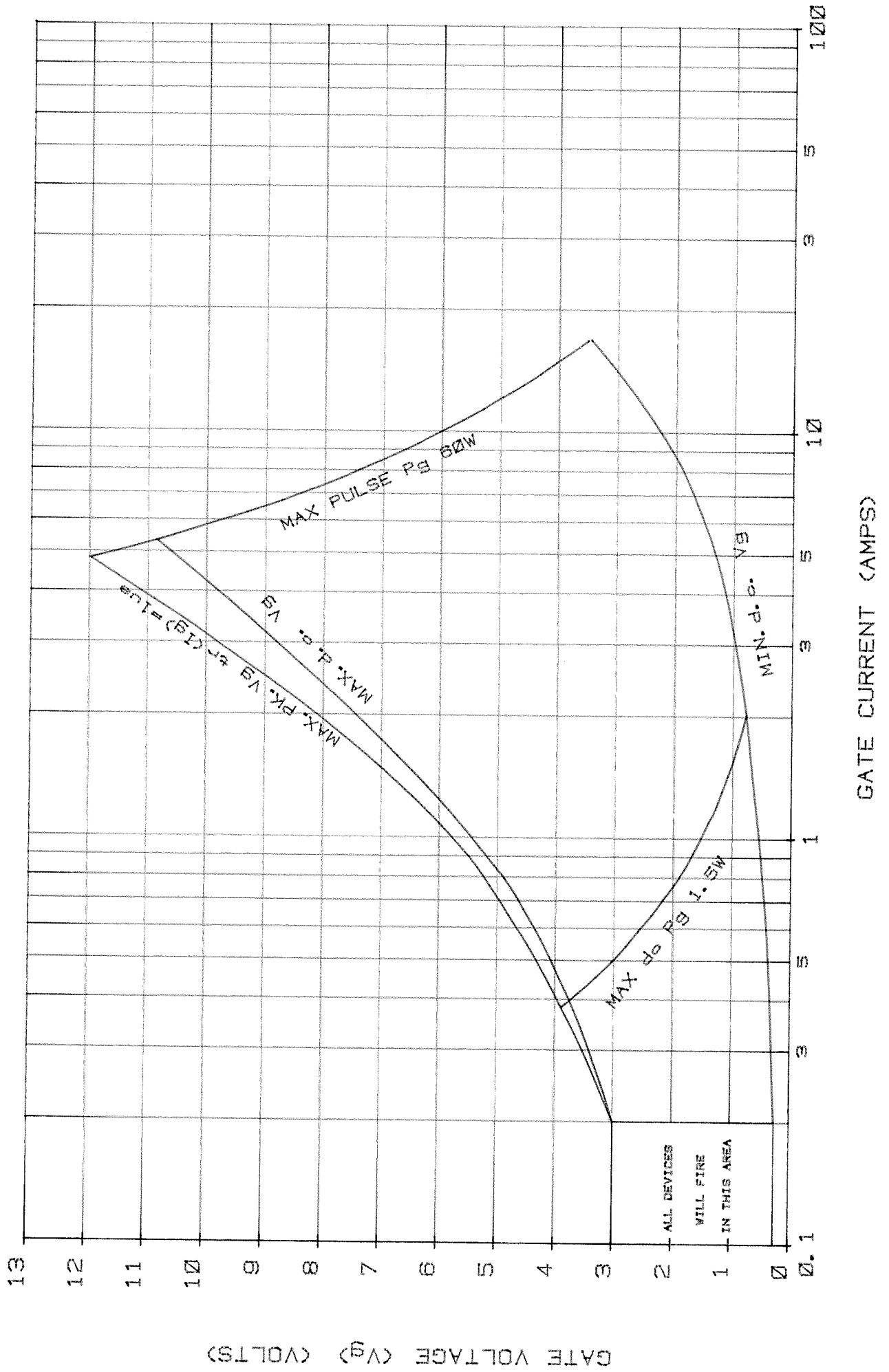


GATE TRIGGERING CHARACTERISTICS

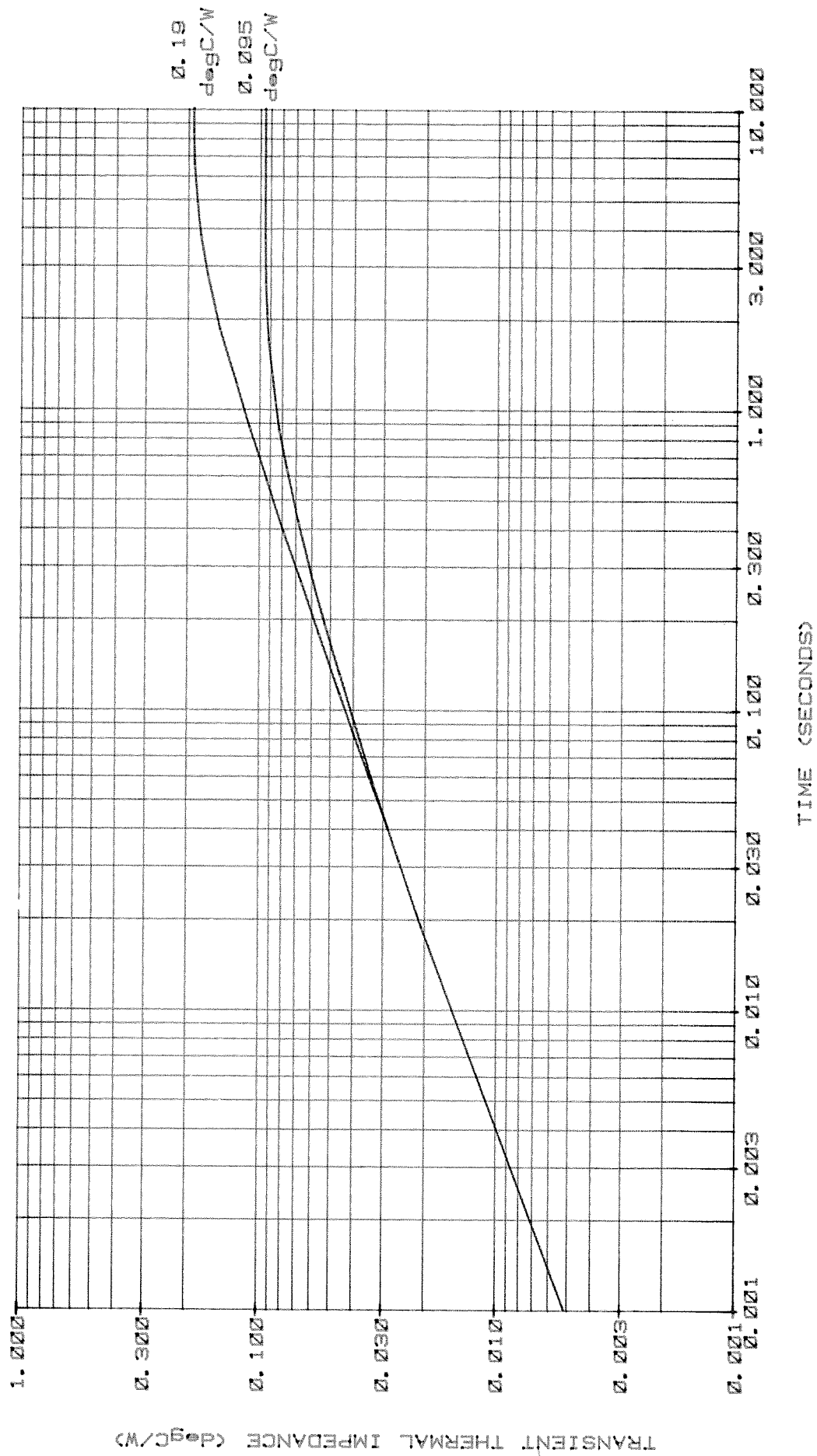
(TRIGGER POINTS OF ALL THYRISTORS LIE IN THE AREAS SHOWN)



GATE CHARACTERISTICS AT 25°C JUNCTION TEMPERATURE

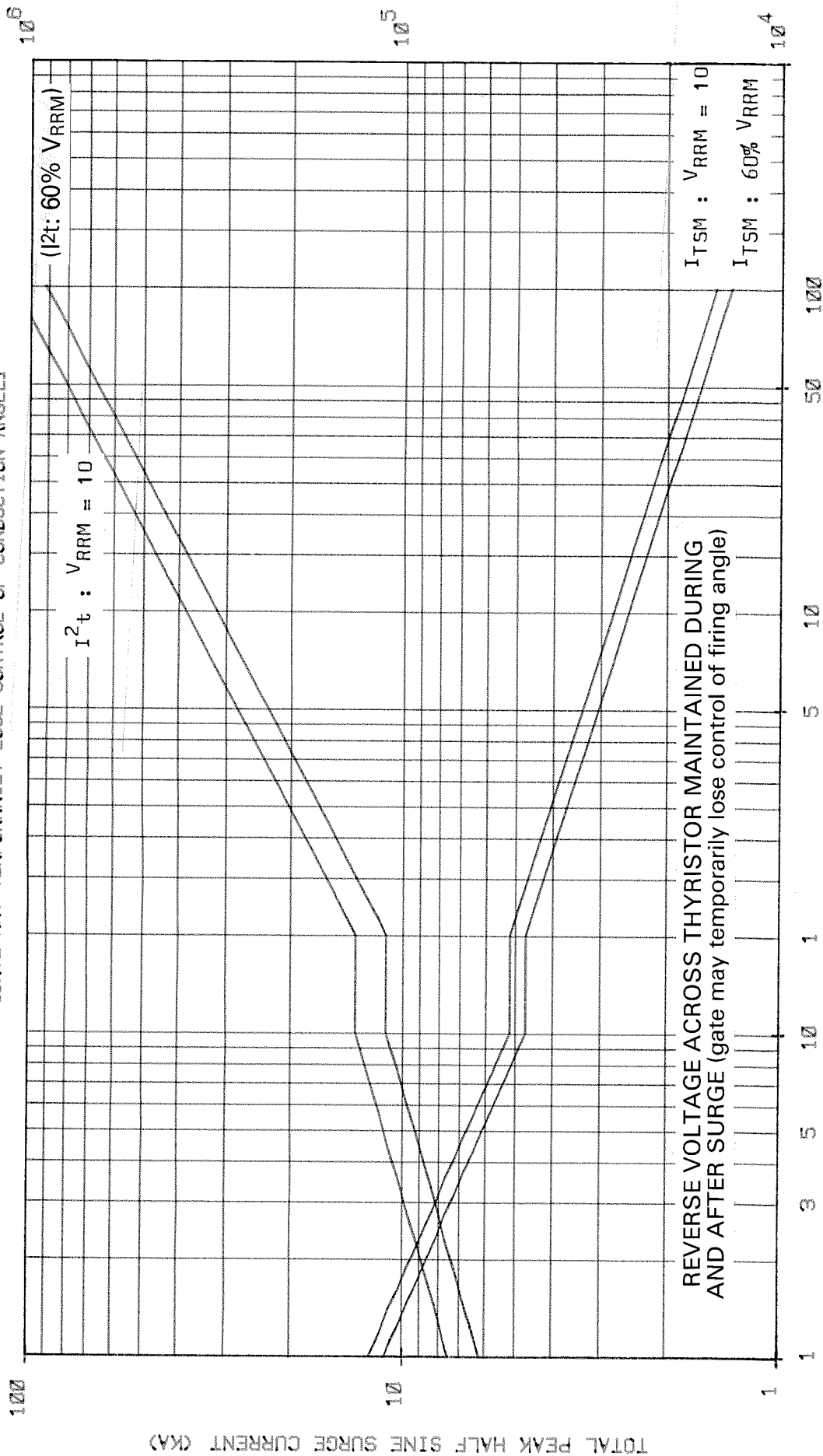


JUNCTION TO HEAT SINK TRANSIENT THERMAL IMPEDANCE



MAXIMUM NON REPETITIVE SURGE CURRENT AT INITIAL JUNCTION TEMPERATURE 125°C

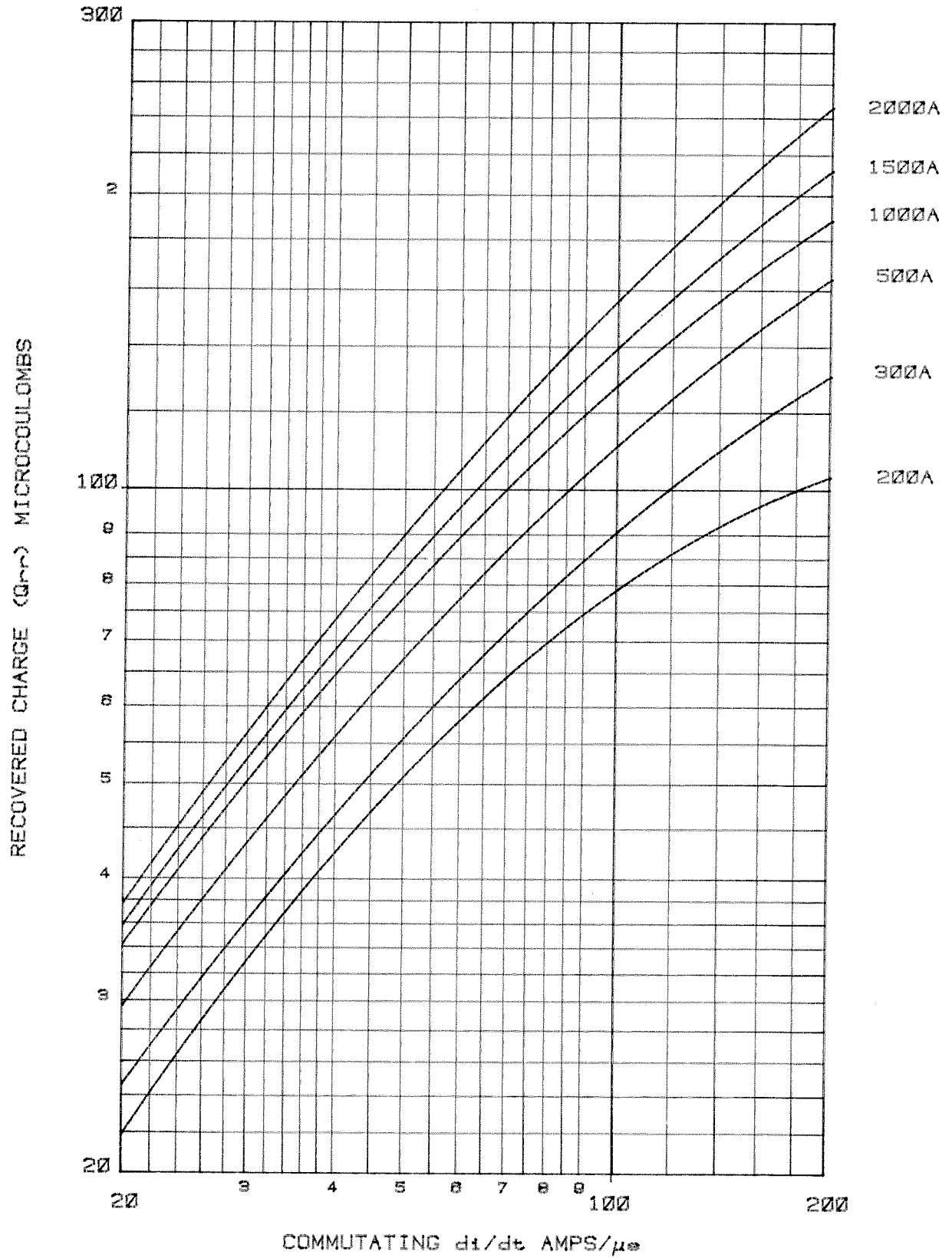
GATE MAY TEMPORARILY LOSE CONTROL OF CONDUCTION ANGLE



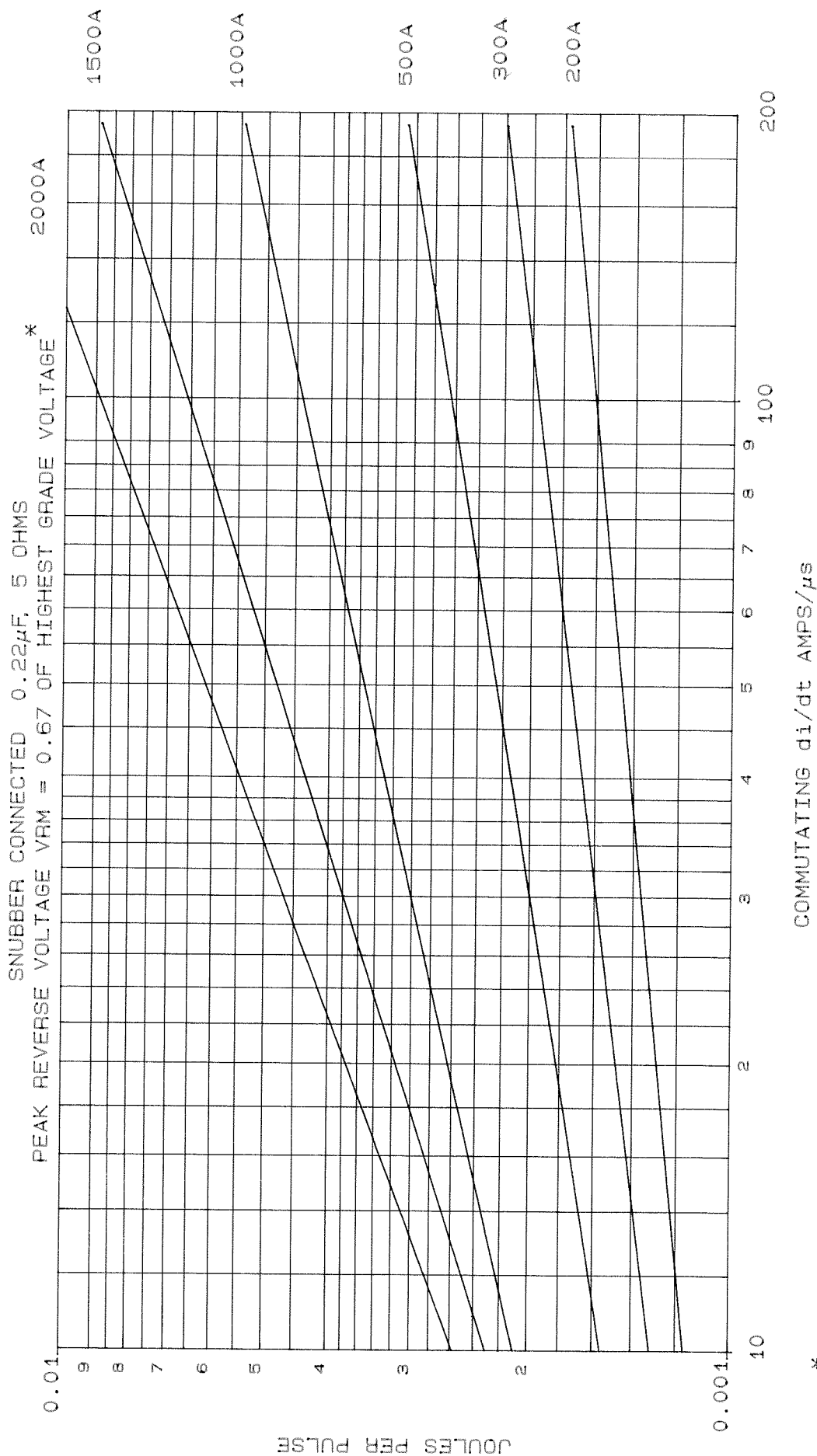
DURATION OF SURGE (cycles at 50 Hz)

DURATION OF SURGE (ms)

TYPICAL RECOVERED CHARGE AT 125°C JUNCTION TEMPERATURE



MAXIMUM REVERSE RECOVERY ENERGY LOSS PER PULSE, 125°C JUNCTION TEMPERATURE



* NOTE: ENERGY PER PULSE SHOULD BE ADJUSTED PRO RATA WITH APPLIED PEAK RECOVERY VOLTAGE

